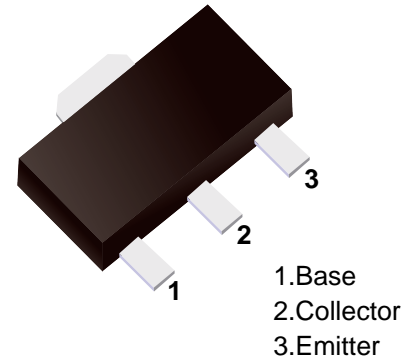


B772

PNP Transistors

Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882



■ Simplified outline(SOT-89)

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CB0}	-40	V
Collector to Emitter Voltage	V_{CE0}	-30	V
Emitter to Base Voltage	V_{EB0}	-6	V
Collector Current to Continuous	I_c	-3	A
Collector Dissipation	P_c	0.5	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

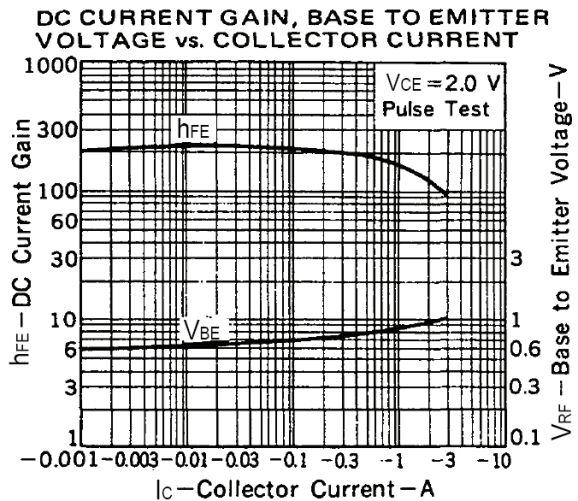
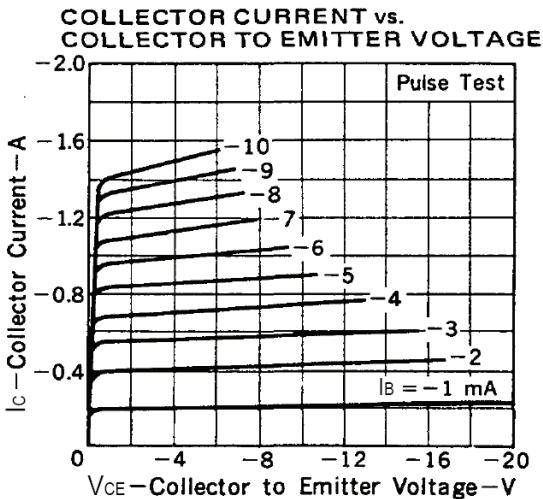
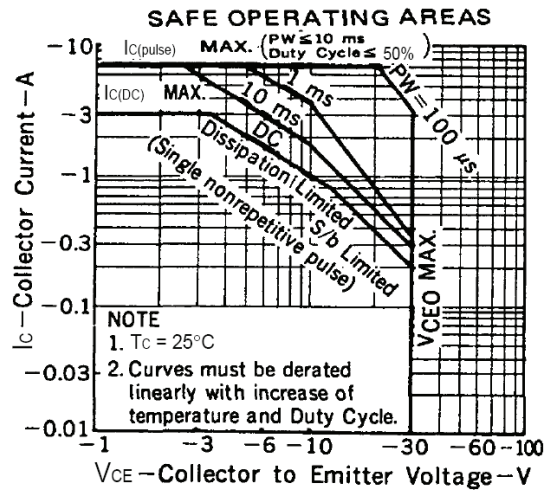
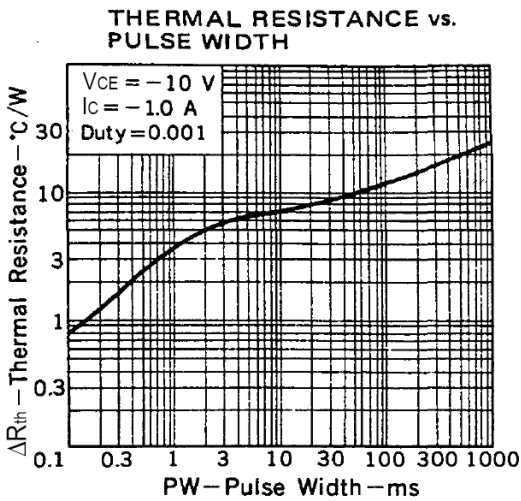
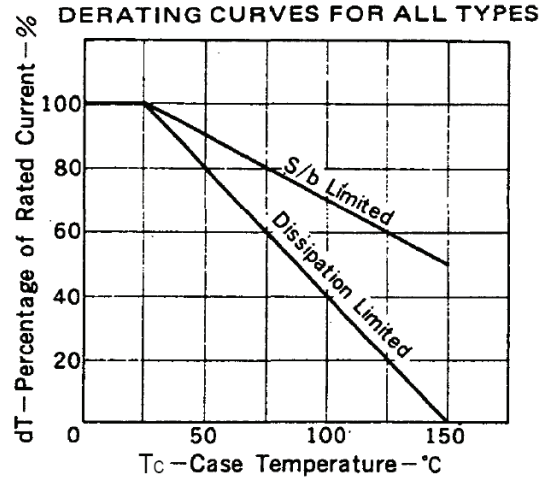
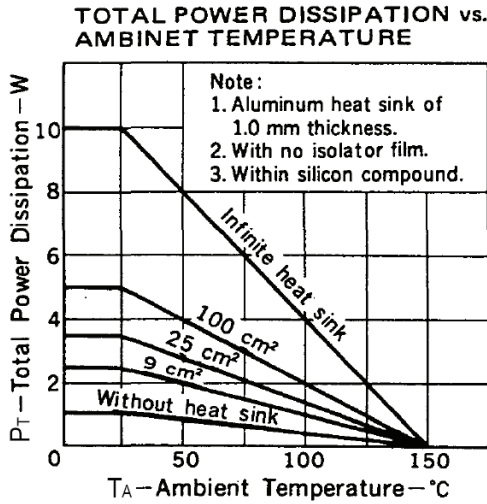
Electrical Characteristics $T_a = 25^\circ\text{C}$

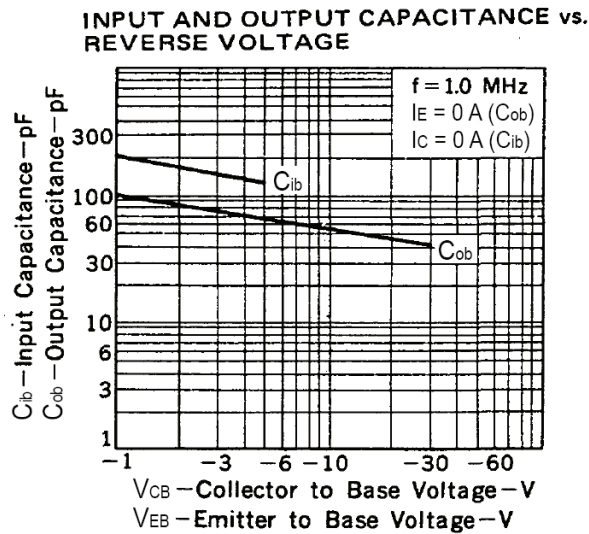
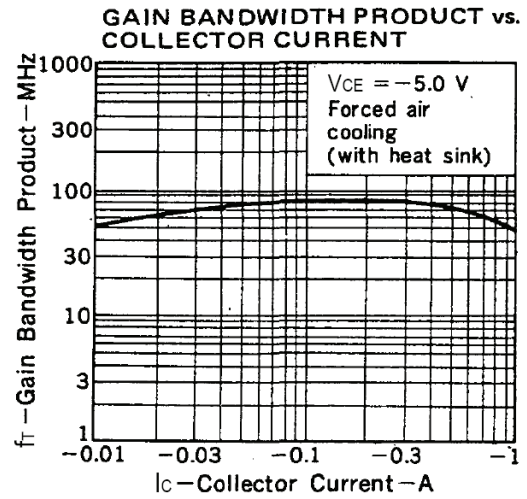
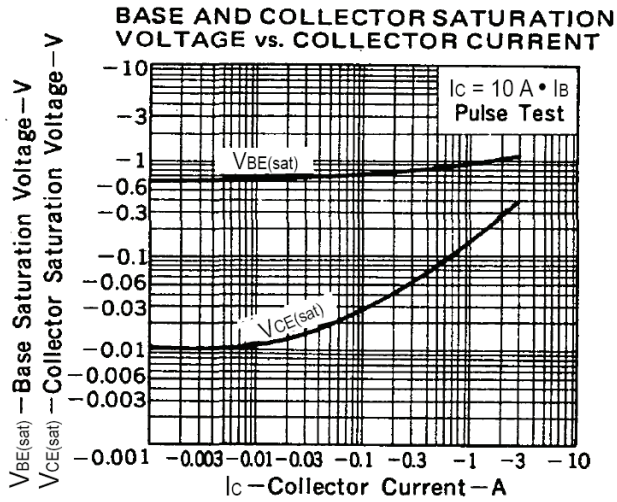
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_c = -100\mu\text{A}$, $I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CE0}	$I_c = -10\text{mA}$, $I_B = 0$	-30			V
Emitter-base breakdown voltage	V_{EB0}	$I_E = -100\mu\text{A}$, $I_c = 0$	-6			V
Collector cut-off current	I_{CB0}	$V_{CB} = -40\text{V}$, $I_E = 0$			-1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -6\text{V}$, $I_c = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}$, $I_c = -1\text{A}$	60		400	
		$V_{CE} = -2\text{V}$, $I_c = -100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -2\text{A}$, $I_B = -0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -2\text{A}$, $I_B = -0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5\text{V}$, $I_c = -0.1\text{mA}$, $f = 10\text{MHz}$	50			MHz

Classification of $h_{fe}(1)$

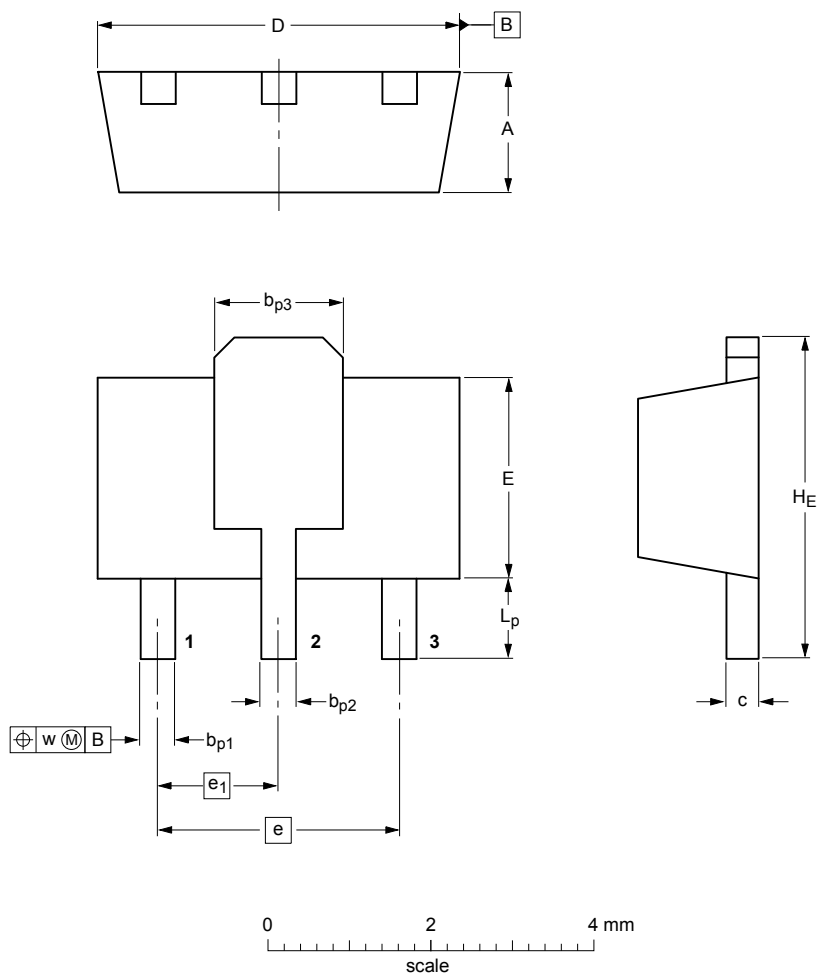
Type	2SB772-R	2SB772-Q	2SB772-P	2SB772-E
Range	60-120	100-200	160-320	200-400

■ Typical Characteristics





■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4			3.75	0.8	